

UTC UNISONIC TECHNOLOGIES CO., LTD

13003EDA

Preliminary

NPN SILICON BIPOLAR TRANSISTORS FOR LOW FREQUENCY AMPLIFICATION

DESCRIPTION

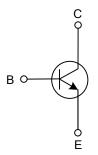
The UTC 13003EDA is a silicon NPN power switching transistor; it uses UTC's advanced technology to provide customers high collector-base breakdown voltage, low reverse leakage current and high reliability, etc.

The UTC 13003EDA is suitable for electronic ballast power switch circuit and the compact electronic energy-saving light.

FEATURES

- * High collector-base breakdown voltage
- * Low reverse leakage current
- * High reliability

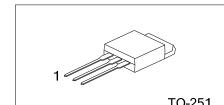
EQUIVALENT CIRCUIT



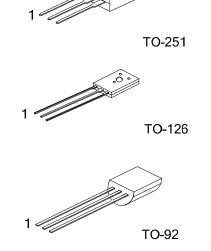
ORDERING INFORMATION

| Ordering Number | | Deekere | Pin Assignment | | | Decking | | |
|---|-------------------|--|----------------|---|---|---------|----------|--|
| Lead Free | Halogen Free | | Package | 1 | 2 | 3 | Packing | |
| 13003EDAL-TM3-T | 13003EDAG-TM3-T | | TO-251 | В | С | Е | Tube | |
| 13003EDAL-T60-F-K | 13003EDAG-T60-F-K | | TO-126 | В | С | Е | Bulk | |
| 13003EDAL-T92-F-B | 13003EDAG-T92-F-B | | TO-92 | В | С | Е | Tape Box | |
| 13003EDAL-T92-F-K | 13003EDAG-T92-F-K | | TO-92 | В | С | Е | Bulk | |
| Note: Pin Assignment: B: Base C: Collector E: Emitter | | | | | | | | |
| (2) (2) (2) (2) | | (1) T: Tube, B: Bluk, K: Bulk | | | | | | |
| | | (2) refer to Pin Assignment | | | | | | |
| | | (3) TM3: TO-251, T60: TO-126, T92: TO-92 | | | | | | |

(4) L: Lead Free, G: Halogen Free



NPN SILICON TRANSISTOR



(4)Lead Free

MARKING

| PACKAGE | MARKING |
|---------|--|
| TO-251 | UTC 13003EDA L: Lead Free P: Halogen Free Lot Code 1 |
| TO-126 | UTC ☐ □□□□ → Pin Code → Data Code 13003EDA□ ↓ L: Lead Free 1 G: Halogen Free |
| TO-92 | UTC 13003EDA UTC L: Lead Free G: Halogen Free Data Code |



Preliminary

NPN SILICON TRANSISTOR

■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise noted)

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|--|------------|------------------|----------|------|
| Collector-Base Voltage | | V _{CBO} | 850 | V |
| Collector-Emitter Voltage | | V _{CEO} | 500 | V |
| Emitter-Base Voltage | | V _{EBO} | 9 | V |
| Collector Current | Continuous | Ιc | 1.3 | А |
| | Peak | I _{CM} | 3 | А |
| Power Dissipation (T _C =25°C) | TO-251 | P _D | 10 | W |
| | TO-126 | | 20 | W |
| | TO-92 | | 1 | W |
| Junction Temperature | | TJ | 150 | °C |
| Storage Temperature Range | | T _{STG} | -55~+150 | °C |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

| PARAMETER | | SYMBOL | RATING | UNIT | |
|---------------------|--------|-----------------|--------|------|--|
| Junction to Ambient | TO-251 | | 95 | °C/W | |
| | TO-126 | θ _{JA} | 100 | | |
| | TO-92 | | 150 | | |
| Junction to Case | TO-251 | | 13 | | |
| | TO-126 | θ _{JC} | 7.5 | °C/W | |
| | TO-92 | | 112 | | |

ELECTRICAL CHARACTERISTICS (T_A =25°C, unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT | |
|--|-------------------------------------|--|------|-----|-----|------|--|
| Collector-Base Breakdown Voltage | BV _{CBO} | I _C =1mA | 850 | | | V | |
| Collector-Emitter Breakdown Voltage | BV _{CEO} | I _C =1mA | 500 | | | V | |
| Emitter-Base Breakdown Voltage | BV_{EBO} | I _E =1mA | 9 | | | V | |
| Collector Cut-Off Current | I _{CBO} | V _{CB} =850V, I _E =0 | | | 0.1 | mA | |
| Collector-Emitter Cut-Off Current | I _{CEO} | V _{CE} =500V, I _B =0 | | | 0.1 | mA | |
| Emitter-Base Cut-Off Current | I _{EBO} | V _{EB} =9V, I _C =0 | | | 0.1 | mA | |
| DC Current Gain (Note) | h _{FE} | V _{CE} =5V, I _C =0.2A | 23 | | 35 | | |
| | h _{FE1} / h _{FE2} | h _{FE1} : V _{CE} =5V, I _C =5mA | 0.75 | 0.0 | | | |
| Low current and high current h _{FE2} h _{FE1} ratio | | h _{FE2} : V _{CE} =5V, I _C =0.2A | 0.75 | 0.9 | | | |
| Collector-Emitter Saturation Voltage (Note) | V _{CE(SAT)} | I _C =0.5A, I _B =0.1A | | 0.2 | 0.8 | V | |
| Base-Emitter Saturation Voltage (Note) | V _{BE(SAT)} | I _C =0.5A, I _B =0.1A | | 0.9 | 1.5 | V | |
| Storage Time | ts | | 2 | | 5 | μs | |
| Rise Time | t _R | UI9600, I _C =100mA | | | 1 | μs | |
| Fall Time | t _F | | | | 1 | μs | |
| Transition Frequency | f⊤ | V _{CE} =10V, I _C =0.1A, f=1MHz | 5 | | | MHz | |
| | | | | | | | |

Note: Pulse test, pulse width tp≤300µs, Duty cycle≤1.5%.



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